



CSD87312Q3E

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Dual 30-V N-Channel NexFET™ Power MOSFETs

FEATURES

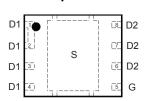
- Common Source Connection
- Ultra Low Drain to Drain On-Resistance
- Space Saving SON 3.3 x 3.3mm Plastic Package
- Optimized for 5V Gate Drive
- Low Thermal Resistance
- Avalanche Rated
- Pb Free Terminal Plating
- RoHS Compliant
- Halogen Free

APPLICATIONS

Adaptor/USB Input Protection for Notebook
PCs and Tablets

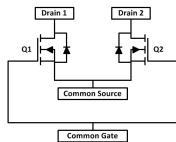
DESCRIPTION

The CSD87312Q3E is a 30V common-source, dual N-channel device designed for adaptor/USB input protection. This SON 3.3 x 3.3mm device has low drain to drain on-resistance that minimizes losses and offers low component count for space constrained multi-cell battery charging applications.



Top View

Circuit Image



PRODUCT SUMMARY

$T_A = 25^{\circ}$	C	TYPICAL VA	UNIT	
V _{DS}	Drain to Source Voltage 30			
Qg	Gate Charge Total (4.5V)	6.3		nC
Q _{gd}	Gate Charge Gate to Drain	0.7	nC	
D	Drain to Drain On Resistance	$V_{GS} = 4.5V$	31	mΩ
R _{DD(on)}	(Q1+Q2)	V _{GS} = 8V 27		mΩ
V _{GS(th)}	Threshold Voltage	1.0	V	

ORDERING INFORMATION

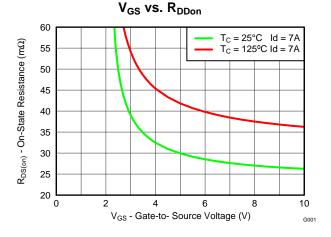
Device	Package	Media	Qty	Ship
CSD87312Q3E	SON 3.3 x 3.3mm Plastic Package	13-Inch Reel	2500	Tape and Reel

ABSOLUTE MAXIMUM RATINGS

$T_A = 2$	5°C	VALUE	UNIT
V_{DS}	Drain to Source Voltage	30	V
V_{GS}	Gate to Source Voltage	+10/-8	V
I _D	Continuous Drain Current, $T_C = 25^{\circ}C^{(1)}$	27	А
I _{DM}	Pulsed Drain Current (2)	45	А
PD	Power Dissipation	2.5	W
T _J , T _{STG}	Operating Junction and Storage Temperature Range	-55 to 150	°C
E _{AS}	Avalanche Energy, single pulse $I_D = 24A$, L = 0.1mH, $R_G = 25\Omega$	29	mJ

(1) Typical R =63°C/W on 1in² (2 oz.) on 0.060" thick FR4PCB

(2) Pulse duration ≤300µs, duty cycle ≤2%



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These devices have limited built-in ESD protection. The leads should be shorted together or the device placed in conductive foam during storage or handling to prevent electrostatic damage to the MOS gates.

ELECTRICAL CHARACTERISTICS $(T_A = 25^{\circ}C \text{ unless otherwise stated})$ **TEST CONDITIONS** MIN TYP MAX UNIT PARAMETER **Static Characteristics** Drain to Source Voltage $V_{GS} = 0V, I_D = 250 \mu A$ V BV_{DSS} 30 $V_{GS} = 0V, V_{DS} = 24V$ Drain to Source Leakage Current 1 μA IDSS $V_{DS} = 0V, V_{GS} = +10/-8V$ 100 I_{GSS} Gate to Source Leakage Current nA $V_{DS} = V_{GS}, I_D = 250 \mu A$ Gate to Source Threshold Voltage 1.3 V V_{GS(th)} 0.8 1.0 $V_{GS} = 4.5V, I_{D} = 7A$ 31 38 mΩ Drain to Drain On Resistance (Q1 + R_{DD(on)} Q2) $V_{GS} = 8V, I_D = 7A$ 27 33 mΩ g_{fs} Transconductance $V_{DS} = 15V, I_{D} = 7A$ 39 S Dynamic Characteristics⁽¹⁾ Input Capacitance Ciss 960 1250 pF Coss **Output Capacitance** $V_{GS} = 0V, V_{DS} = 15V, f = 1MHz$ 190 247 pF C_{rss} 12 16 **Reverse Transfer Capacitance** pF R_{G} Series Gate Resistance 5 10 Ω 8.2 Qg Gate Charge Total (4.5V) 6.3 nC Gate Charge Gate to Drain 0.7 nC Q_{gd} $V_{DS} = 15V, I_{D} = 7A$ Q_{gs} Gate Charge Gate to Source 1.9 nC Gate Charge at Vth 1.0 nC Q_{g(th)} **Output Charge** $V_{DS} = 15V, V_{GS} = 0V$ 4.0 Q_{oss} nC Turn On Delay Time 7.8 ns t_{d(on)} tr **Rise Time** 16 ns V_{DS} = 15V, V_{GS} = 4.5V, I_{DS} = 7A, R_G = 2 Ω Turn Off Delay Time 17 ns t_{d(off)} Fall Time 2.9 tf ns Diode Characteristics⁽¹⁾ **Diode Forward Voltage** $I_{SD} = 7A, V_{GS} = 0V$ V_{SD} 0.8 1 V 5.3 Qrr **Reverse Recovery Charge** nC V_{DS} = 15V, I_F = 7A, di/dt = 300A/µs **Reverse Recovery Time** 12.2 t_{rr} ns

(1) All Dynamic and Diode Characteristics were measured with respect to one of the two drains, with the other left floating.

THERMAL CHARACTERISTICS

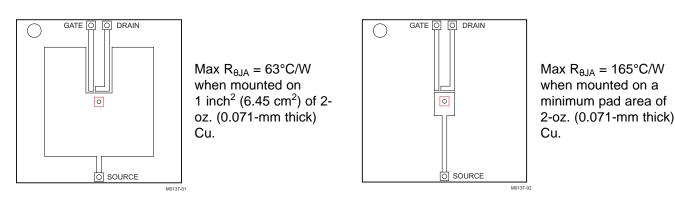
 $(T_A = 25^{\circ}C \text{ unless otherwise stated})$

	PARAMETER	MIN	TYP	MAX	UNIT
$R_{\theta JC}$	Thermal Resistance Junction to Case ⁽¹⁾			4.2	°C/W
$R_{\theta J A}$	Thermal Resistance Junction to Ambient ⁽¹⁾⁽²⁾			63	°C/W

 $R_{\theta JC}$ is determined with the device mounted on a 1-inch² (6.45-cm²), 2-oz. (0.071-mm thick) Cu pad on a 1.5-inch x 1.5-inch (3.81-cm x 3.81-cm), 0.06-inch (1.52-mm) thick FR4 PCB. $R_{\theta JC}$ is specified by design, whereas $R_{\theta JA}$ is determined by the user's board design. Device mounted on FR4 material with 1-inch² (6.45-cm²), 2-oz. (0.071-mm thick) Cu. (1)

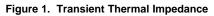


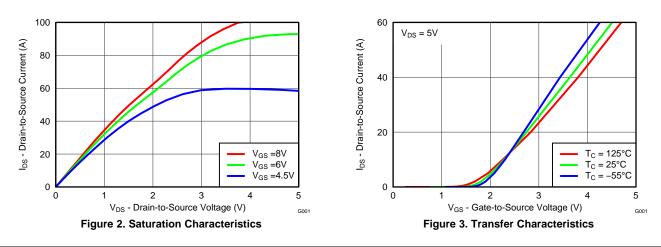
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TYPICAL MOSFET CHARACTERISTICS ($T_A = 25^{\circ}C$ unless otherwise stated)

10 10% Single Pulse 2% 50% 5% 30% 1% Z[0JA] - Normalized Thermal Impedance 1 0.1 Duty Cycle =t₁/t₂ 0.01 Typ Rth_{JA} = 130°C/W 0.001 $\Delta T_i = P * Zth_{JA} * Rth_{JA}$ 0.0001 0.01 0.1 1 10 100 1000 t_p - Pulse Duration (s) G001





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TYPICAL MOSFET CHARACTERISTICS (continued)

 $(T_A = 25^{\circ}C \text{ unless otherwise stated})$

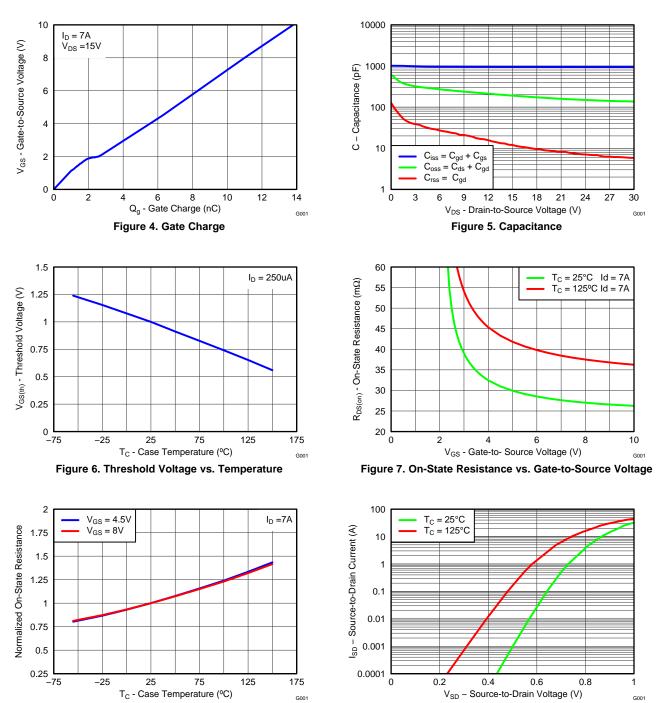


Figure 8. Normalized On-State Resistance vs. Temperature

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Figure 9. Typical Diode Forward Voltage



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TYPICAL MOSFET CHARACTERISTICS (continued)

 $(T_A = 25^{\circ}C \text{ unless otherwise stated})$

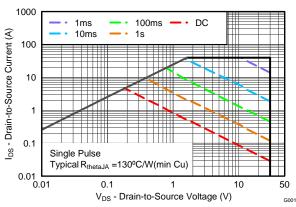
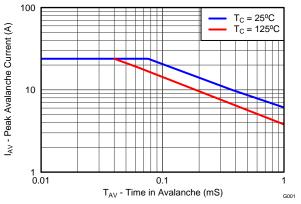
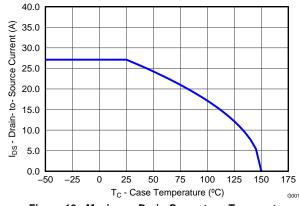


Figure 10. Maximum Safe Operating Area





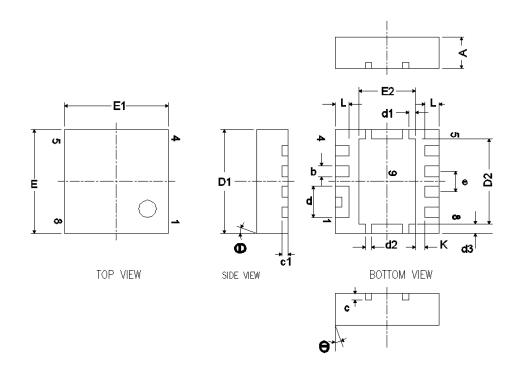




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MECHANICAL DATA

Q3E Package Dimensions



DIM	MILLIMETERS						
DIM	MIN	MAX					
A	0.850	1.050					
b	0.280	0.400					
С	0.150	0.250					
c1	0.150	0.250					
d	0.940	1.040					
d1	0.160	0.260					
d2	0.150	0.250					
d3	0.250	0.350					
D1	3.200	3.400					
D2	2.650	2.750					
E	3.200	3.400					
E1	3.200	3.400					
E2	1.750	1.850					
е	0.650) TYP					
L	0.400	0.500					
θ	0° -						
К	0.300 Тур						

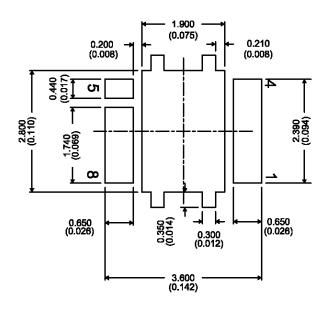
Notes:

- 1. Pin 1-4: Drain 1
- 2. Pin 5: Gate
- 3. Pin 6-8: Drain 2
- 4. Pin 9: Source

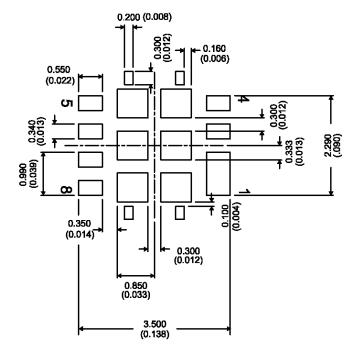


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Recommended PCB Pattern



Recommended Stencil Opening

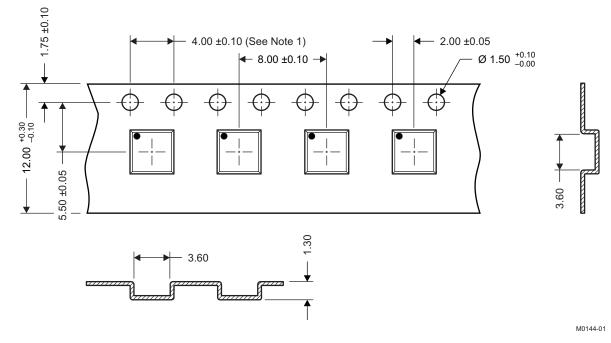


For recommended circuit layout for PCB designs, see application note SLPA005 – Reducing Ringing Through PCB Layout Techniques.



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Notes:

- 1. 10 sprocket hole pitch cumulative tolerance ±0.2
- 2. Camber not to exceed 1mm IN 100mm, noncumulative over 250mm
- 3. Material:black static dissipative polystyrene
- 4. All dimensions are in mm (unless otherwise specified)
- 5. Thickness: 0.30 ±0.05mm
- 6. MSL1 260°C (IR and Convection) PbF Reflow Compatible



24-Jan-2013

PACKAGING INFORMATION

Orderable Device	Status	Package Type	Package	Pins	Package Qty	Eco Plan	Lead/Ball Finish	MSL Peak Temp	Op Temp (°C)	Top-Side Markings	Samples
	(1)		Drawing			(2)		(3)		(4)	
CSD87312Q3E	ACTIVE	VSON	DPB	8	2500	Pb-Free (RoHS Exempt)	CU NIPDAU	Level-1-260C-UNLIM	-55 to 150	87312E	Samples
CSD87312Q3E-ASY	PREVIEW	VSON	DPB	8		TBD	Call TI	Call TI	-55 to 150		

⁽¹⁾ The marketing status values are defined as follows:

ACTIVE: Product device recommended for new designs.

LIFEBUY: TI has announced that the device will be discontinued, and a lifetime-buy period is in effect.

NRND: Not recommended for new designs. Device is in production to support existing customers, but TI does not recommend using this part in a new design.

PREVIEW: Device has been announced but is not in production. Samples may or may not be available.

OBSOLETE: TI has discontinued the production of the device.

⁽²⁾ Eco Plan - The planned eco-friendly classification: Pb-Free (RoHS), Pb-Free (RoHS Exempt), or Green (RoHS & no Sb/Br) - please check http://www.ti.com/productcontent for the latest availability information and additional product content details.

TBD: The Pb-Free/Green conversion plan has not been defined.

Pb-Free (RoHS): TI's terms "Lead-Free" or "Pb-Free" mean semiconductor products that are compatible with the current RoHS requirements for all 6 substances, including the requirement that lead not exceed 0.1% by weight in homogeneous materials. Where designed to be soldered at high temperatures, TI Pb-Free products are suitable for use in specified lead-free processes. **Pb-Free (RoHS Exempt):** This component has a RoHS exemption for either 1) lead-based flip-chip solder bumps used between the die and package, or 2) lead-based die adhesive used between the die and leadframe. The component is otherwise considered Pb-Free (RoHS compatible) as defined above.

Green (RoHS & no Sb/Br): TI defines "Green" to mean Pb-Free (RoHS compatible), and free of Bromine (Br) and Antimony (Sb) based flame retardants (Br or Sb do not exceed 0.1% by weight in homogeneous material)

⁽³⁾ MSL, Peak Temp. -- The Moisture Sensitivity Level rating according to the JEDEC industry standard classifications, and peak solder temperature.

⁽⁴⁾ Only one of markings shown within the brackets will appear on the physical device.

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PACKAGE MATERIALS INFORMATION

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TAPE AND REEL INFORMATION





QUADRANT ASSIGNMENTS FOR PIN 1 ORIENTATION IN TAPE



*All dimensions	are nominal
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Device	Package Type	Package Drawing		SPQ	Reel Diameter (mm)	Reel Width W1 (mm)	A0 (mm)	B0 (mm)	K0 (mm)	P1 (mm)	W (mm)	Pin1 Quadrant
CSD87312Q3E	VSON	DPB	8	2500	330.0	16.4	3.6	3.6	1.2	8.0	16.0	Q1

TEXAS INSTRUMENTS

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PACKAGE MATERIALS INFORMATION

14-Mar-2013



*All dimensions are nominal

Device	Package Type	Package Drawing	Pins	SPQ	Length (mm)	Width (mm)	Height (mm)
CSD87312Q3E	VSON	DPB	8	2500	367.0	367.0	38.0

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